

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of)

Hideo YAMANAKA et al.)

Serial No. 09/646,680)

Filed: September 20, 2000)

Group Art Unit: 1763

Ex'r: Parviz Hassanzadeh

FOR: FILM FORMING METHOD AND FILM)
FORMING APPARATUS)RESPONSE ELECTING INVENTIONCommissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Official Action dated December 21, 2001
(Paper No. 5), please amend the above-identified application as
follows:

IN THE SPECIFICATION:

Please rewrite the following paragraphs as set forth below
in clean form. Additionally, in accordance with 37 CFR
1.121(b)(1)(iii), the amended paragraphs are set forth in a
marked-up version in the pages attached to this Amendment.

Beginning at page 2, line 7,

(1) Lack of uniformity and fluctuation of a plasma field,
and a non-uniform electric field in plasma-induced electric
charges are generated. These may cause damages and short
circuits t the transistor (e.g., charge-up or discharge breakdown
of a gate oxide film, discharge between wirings, and the like).

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